

dipping a seed crystal into a silicon melt to form a crystal ingot, and applying a horizontal magnetic field with a magnetic field strength of a first preset value; wherein, in an axial direction of the crystal ingot, a first distance between a maximum gauss plane of the horizontal magnetic field and a liquid surface of the silicon melt is less than a second preset value

during a body process of the crystal ingot growth, applying a cusp magnetic field with a magnetic field strength of a third preset value; wherein a zero gauss plane of the cusp magnetic field is located at an R-arc part of the crucible

FIG. 1

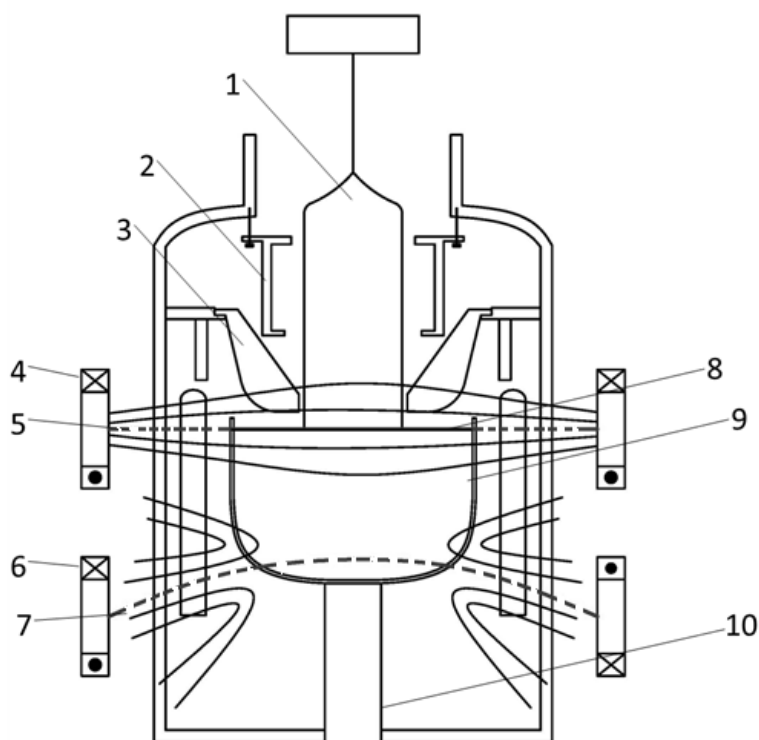


FIG. 2

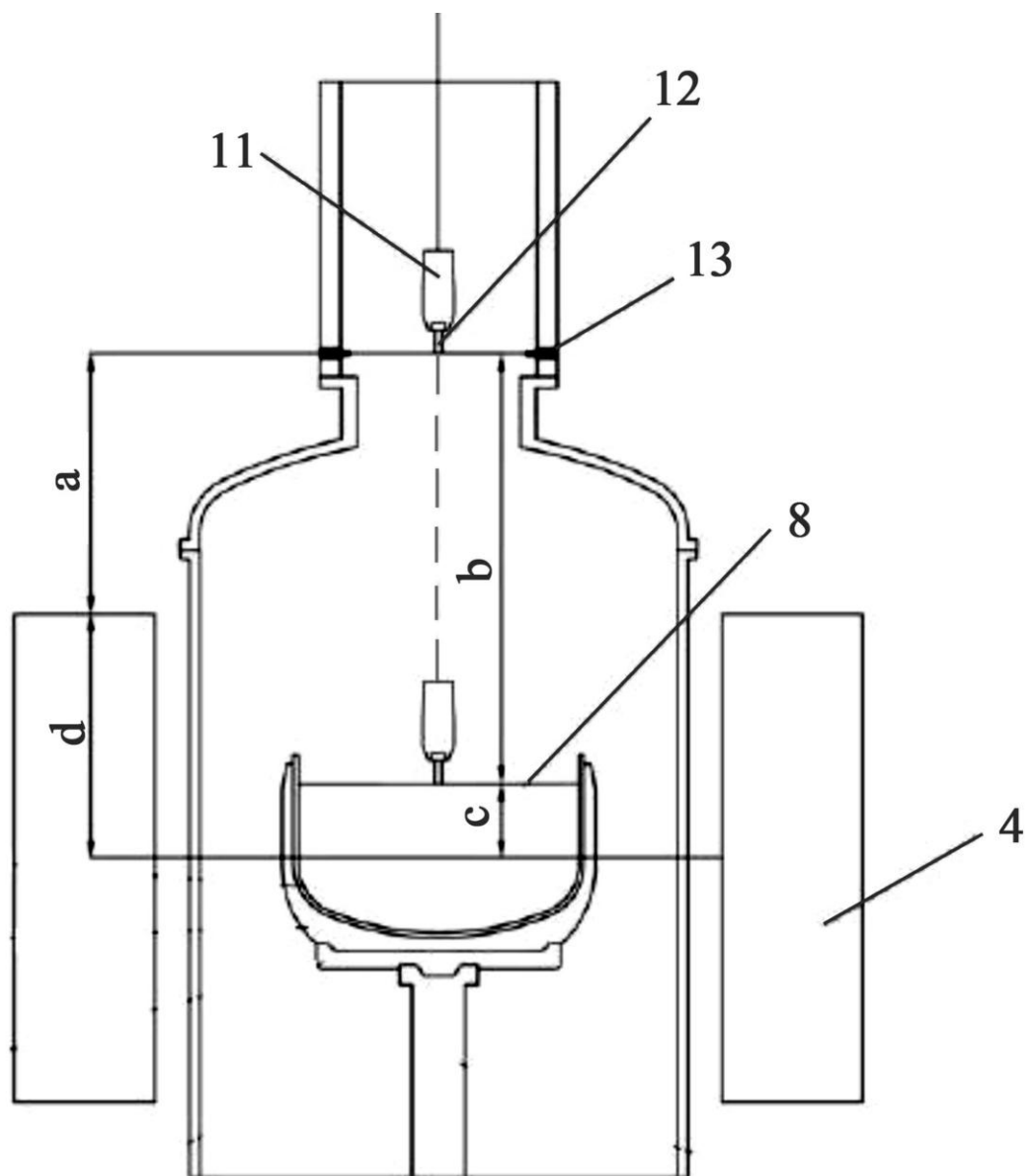


FIG. 3